

Wavelength	Type	Technology	Case
Infrared	water clear	AlGaAs/GaAs	5 mm plastic lens

		Description
		Selective photodiode mounted in standard 5 mm package without standoff. Narrow response range (740 nm peak) by means of integrated filter
Note: Special packages with standoff available on request		

Applications

Optical communications, safety equipment, light barriers

Miscellaneous Parameters

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Active area		A	0.62	mm ²
Temperature coefficient of I _D		T _C (I _D)	5	%/K
Operating temperature range		T _{amb}	-20 to +85	°C
Storage temperature range		T _{stg}	-40 to +125	°C
Soldering Temperature	t ≤ 3 s, 3 mm from case	T _{sld}	260	°C
Acceptance angle at 50% S _λ		φ	20	deg.

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Breakdown voltage ¹⁾	I _R = 10 µA	V _R	5			V
Dark current	V _R = 5 V	I _D		40	200	pA
Peak sensitivity wavelength	V _R = 0 V	λ _p		740		nm
Responsivity at λ _p	V _R = 0 V	S _λ		0.5		A/W
Spectral range at 10 %	V _R = 0 V	λ _{0.5}	680		770	nm
Spectral bandwidth at 50%	V _R = 0 V	Δλ _{0.4}		80		nm
Shunt resistance	V _R = 10 mV	R _{SH}		300		GΩ
Noise equivalent power	λ = 740 nm	NEP		7.2x10 ⁻¹⁵		W/√Hz
Specific detectivity	λ = 740 nm	D*		1.1x10 ¹³		cm · √Hz · W ⁻¹
Junction capacitance	V _R = 0 V	C _J		120		pF
Switching time (R _L = 50 Ω)	V _R = 5 V	t _r , t _f		170		ns
Photo-current at λ _p ²⁾	V _R = 0 V E _e = 1mW/cm ²	I _{Ph}		15		µA

¹⁾for information only

²⁾Halogen lamp source with appropriate filter

Note: All measurements carried out with EPIGAP equipment

Labeling

Type	Lot N°	R _D (typ.) [GΩ]	Quantity
EPD-740-5-0.9			

